

2SB1416

Silicon PNP epitaxial planar type

For low-frequency power amplification

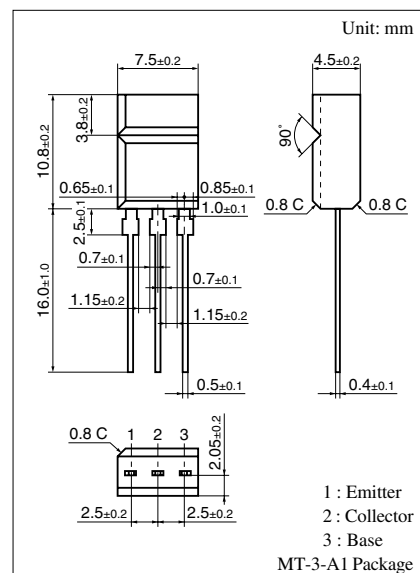
Complementary to 2SD2136

■ Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
- Low collector to emitter saturation voltage $V_{CE(sat)}$
- Allowing automatic insertion with radial taping

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|------------------------------|-----------|-------------|------------------|
| Collector to base voltage | V_{CBO} | -60 | V |
| Collector to emitter voltage | V_{CEO} | -60 | V |
| Emitter to base voltage | V_{EBO} | -5 | V |
| Peak collector current | I_{CP} | -5 | A |
| Collector current | I_C | -3 | A |
| Collector power dissipation | P_C | 1.5 | W |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

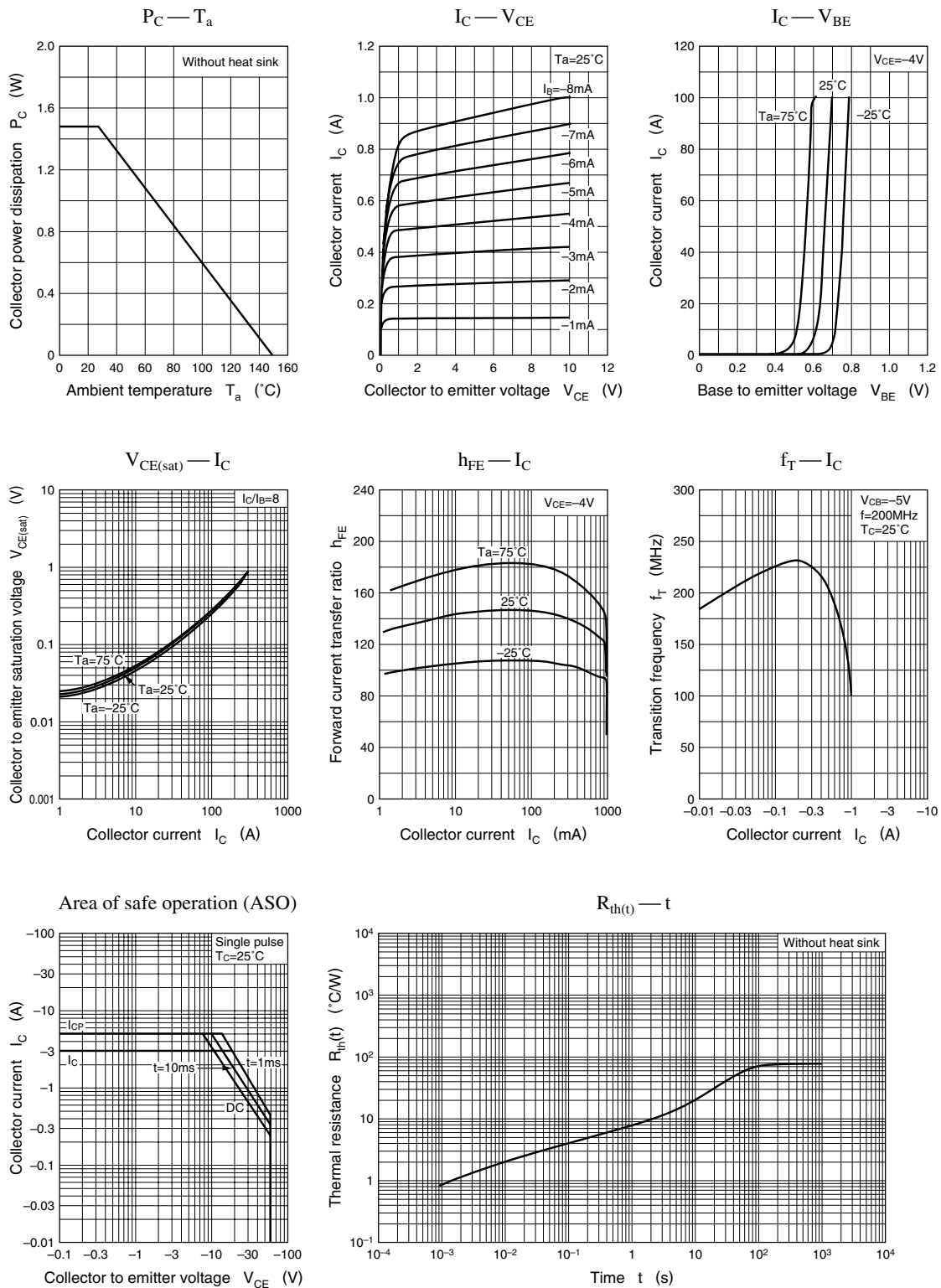


■ Electrical Characteristics $T_C = 25^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|---|---------------|--|-----|-----|------|---------------|
| Collector cutoff current | I_{CES} | $V_{CE} = -60\text{ V}, V_{BE} = 0$ | | | -200 | μA |
| | I_{CEO} | $V_{CE} = -30\text{ V}, I_B = 0$ | | | -300 | μA |
| Emitter cutoff current | I_{EBO} | $V_{EB} = -5\text{ V}, I_C = 0$ | | | -1 | mA |
| Collector to emitter voltage | V_{CEO} | $I_C = -30\text{ mA}, I_B = 0$ | -60 | | | V |
| Forward current transfer ratio | h_{FE1}^* | $V_{CE} = -4\text{ V}, I_C = -1\text{ A}$ | 40 | | 250 | |
| | h_{FE2} | $V_{CE} = -4\text{ V}, I_C = -3\text{ A}$ | 10 | | | |
| Collector to emitter saturation voltage | $V_{CE(sat)}$ | $I_C = -3\text{ A}, I_B = -0.375\text{ A}$ | | | -1.8 | V |
| Base to emitter saturation voltage | $V_{BE(sat)}$ | $V_{CE} = -4\text{ V}, I_C = -3\text{ A}$ | | | -1.2 | V |
| Transition frequency | f_T | $V_{CB} = -5\text{ V}, I_E = 0.1\text{ A}, f = 200\text{ MHz}$ | | | 270 | MHz |
| Turn-on time | t_{on} | $I_C = -1\text{ A}, I_{B1} = -0.1\text{ A}, I_{B2} = 0.1\text{ A}$ | | 0.5 | | μs |
| Storage time | t_{stg} | | | 1.2 | | μs |
| Fall time | t_f | | | 0.3 | | μs |

Note) *: Rank classification

| Rank | P | Q | R |
|-----------|----------|-----------|------------|
| h_{FE1} | 40 to 90 | 70 to 150 | 120 to 250 |



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